

(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property  
Organization  
International Bureau



(43) International Publication Date  
29 September 2005 (29.09.2005)

PCT

(10) International Publication Number  
**WO 2005/091394 A1**

(51) International Patent Classification<sup>7</sup>: **H01L 51/00**

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(21) International Application Number:  
**PCT/JP2005/005306**

(22) International Filing Date: 16 March 2005 (16.03.2005)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:  
2004-087077 24 March 2004 (24.03.2004) JP

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(81) Designated States (unless otherwise indicated, for every kind of national protection available): AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SM, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW.

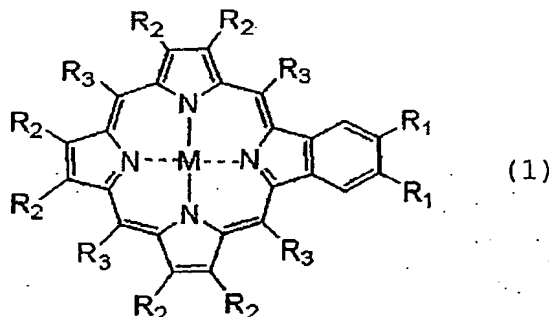
(84) Designated States (unless otherwise indicated, for every kind of regional protection available): ARIPO (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IS, IT, LT, LU, MC, NL, PL, PT, RO, SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Published:

— with international search report

For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.

(54) Title: FIELD EFFECT TRANSISTOR AND METHOD OF PRODUCING SAME



(57) Abstract: A field effect transistor is provided which comprises an organic semiconductor layer comprising a compound having a monobenzoporphyrin skeleton represented by the general formula (1): wherein R<sub>1</sub> and R<sub>2</sub> are independently selected from the group consisting of a hydrogen atom, a halogen atom, a hydroxyl group, and alkyl, alkenyl, oxyalkyl, thioalkyl, alkyl ester and aryl groups each having 1 to 12 carbon atoms with the proviso that adjacent R<sub>1</sub> may be the same or different and adjacent R<sub>2</sub> may be the same or different and that at least two of R<sub>2</sub> are not hydrogen atoms; R<sub>3</sub> is a hydrogen atom or an aryl group; and M denotes two hydrogen atoms, a metal atom or a metal oxide.

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